

This diagram shows a cross-sectional view of a semiconductor device. It features a substrate with a first conductive layer (20) and a second conductive layer (22). A second conductive layer (26) is formed on top of the first conductive layer (20). The second conductive layer (26) is patterned into a series of raised regions (28, 30, 34) and recessed regions (32). The raised regions (28, 30, 34) are separated by recessed regions (32). The second conductive layer (26) is formed on top of the first conductive layer (20) and is patterned into a series of raised regions (28, 30, 34) and recessed regions (32). The raised regions (28, 30, 34) are separated by recessed regions (32). The second conductive layer (26) is formed on top of the first conductive layer (20) and is patterned into a series of raised regions (28, 30, 34) and recessed regions (32). The raised regions (28, 30, 34) are separated by recessed regions (32).

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FIG. 2
BACKGROUND ART

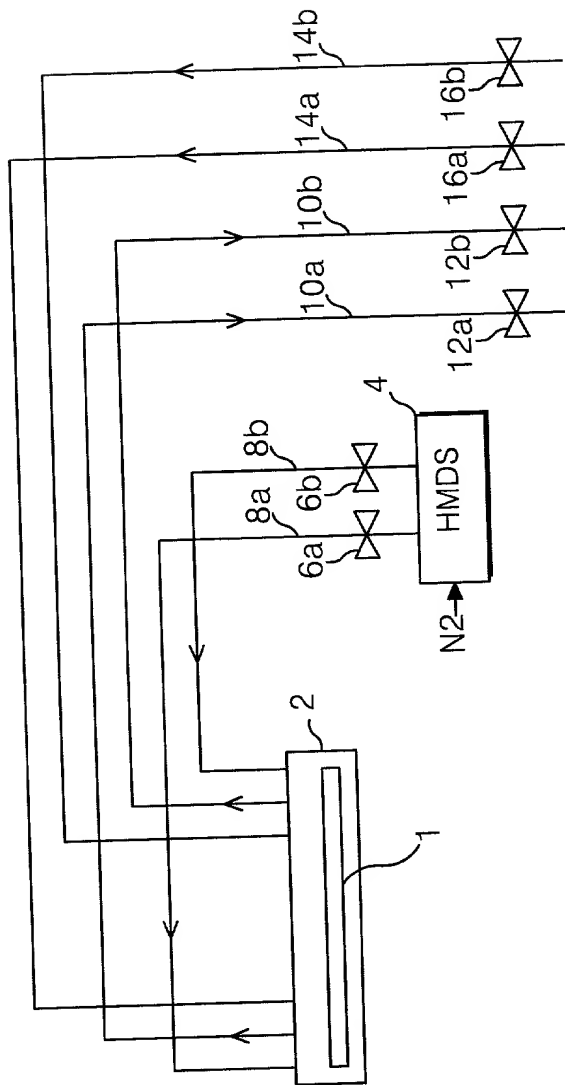
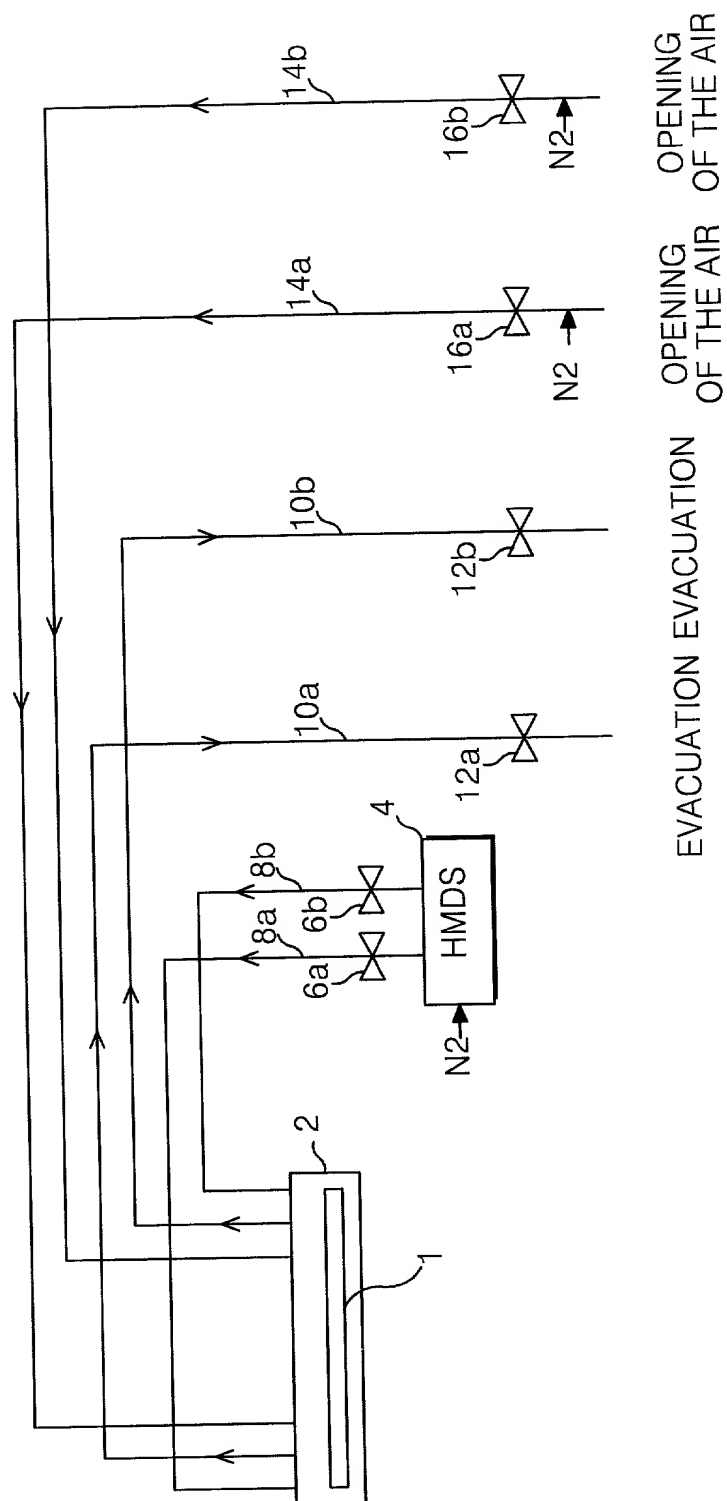


FIG. 3



EVACUATION EVACUATION

OPENING OF THE AIR